ABSTRACT

SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD OF THE SEMICONDUCTOR DEVICE

The present technology provides a semiconductor device. The semiconductor device includes a stack including insulating patterns and conductive patterns stacked alternately with each other, a channel layer including a first channel portion protruding out of the stack and a second channel portion in the stack, and passing through the stack, and a conductive line surrounding the first channel portion, and the first channel portion includes metal silicide.

FIG. 1B